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(54) **Title:** SEMICONDUCTING SILOXANE COMPOSITIONS FOR THIN FILM TRANSISTOR DEVICES, AND MAKING AND USING THE SAME

(57) **Abstract:** Semiconducting siloxane compositions and methods for manufacturing and use thereof in preparing organic thin-film transistors (OTFTs) are described. The semiconducting siloxane compositions can be crosslinked products of polymeric/monomeric compositions that include silane-derivatized crosslinkable organic p-type compounds and p-type semiconducting polymers.



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